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**INFORMATION DISCLOSURE  
STATEMENT BY APPLICANT**

Filed: November 29, 2007

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Sheet 1 of 3

**Complete if Known**

Application Number	Unassigned 10590485
Filing Date	04/02/08
First Named Inventor	Igor BARGATIN et al.
Group Art Unit	Unassigned 2855
Examiner Name	Unassigned M. Noori
Attorney Docket Number	049411-0340

**U.S. PATENT DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code <sup>2</sup> (if known)			
/MN/	A1	2002/0166962	A1	ROUKES et al.	11/14/2002	
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**FOREIGN PATENT DOCUMENTS**

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		Office <sup>3</sup>	Number <sup>4</sup>	Kind Code <sup>5</sup> (if known)				
/MN/	A30	WO	2003/095616	A2	California Inst. of Tech.	11/20/2003		
/MN/	A31	WO	2003/095617	A2	California Inst. of Tech.	11/20/2003		
/MN/	A32	WO	2004/041998	A2	California Inst. of Tech.	05/21/2004		

Examiner Signature

/Max Noori/

Date Considered

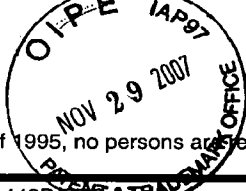
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**NON PATENT LITERATURE DOCUMENTS**

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>6</sup>
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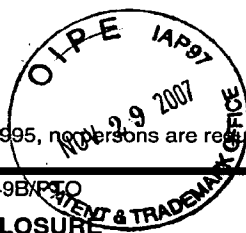
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